

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-34 (canceled).

Claim 35 (previously presented): A copper alloy sputtering target for forming a thin film seed layer for semiconductor wiring, consisting of:

0.01 to less than 0.5wt% of Al for preventing coagulation upon plating on the seed layer;
at least one of Mn or Si or both in a total amount of 0.03wtppm to 0.25wtppm for improving oxidation resistance;
at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 0.13wtppm to 1.0wtppm for improving oxidation resistance; and
a remainder being copper.

Claim 36 (previously presented): A copper alloy sputtering target according to claim 35 wherein said at least one of Mn or Si or both is Mn.

Claim 37 (previously presented): A copper alloy sputtering target according to claim 35, wherein said copper alloy sputtering target contains 0.05 to 0.2wt% of Al, and wherein said total

amount of said at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As is 0.13wtppm to 0.3wtppm.

Claim 38 (previously presented): A copper alloy sputtering target according to claim 35, wherein said copper alloy sputtering target has an average crystal grain size of 100 μ m or less and an average grain size variation within \pm 20%.

Claims 39-42 (canceled).